

REMARKS

By this Amendment, Applicant has amended claims 1, 3-5 and 7-11 and added claims 12 and 13. Claims 1-13 are pending in the application. In view of the amendments and remarks contained herein, favorable reconsideration in this application is respectfully requested.

By this Amendment, Applicant has corrected informalities noted in the specification. Favorable consideration and entry thereof is requested.

The Examiner objected to the drawings as including reference signs not appearing in the specification, namely "X" and "Y". Applicant invites the Examiner's attention to the specification at page 8, where "X" and "Y" are identified with reference to the corresponding areas indicated in Figure 4.

The Examiner rejected claims 1-11 under 35 U.S.C. 112, second paragraph, as being indefinite. By this Amendment, Applicant has amended the claims to correct the informalities identified by the Examiner and presents the claims as being in compliance with 35 U.S.C. 112, second paragraph. In response to the Examiner's further comments, Applicant notes that what is meant by the terms "fine line pattern", "pad pattern", etc., is as defined in the specification and that these terms would be understood as to their meaning by persons of ordinary skill in the art. Favorable reconsideration of the claims as amended is requested.

Attached hereto is a marked-up version of the changes made to the application by the current amendment. The attached pages are captioned "Version with Markings to Show Changes Made".

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Atty. Docket No.: P67358US0

There being no prior art rejection, the claims as amended are in condition for allowance. Should the Examiner have any questions or comments, the Examiner is cordially invited to telephone the undersigned attorney so that the present application can receive an early Notice of Allowance.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

On page 4, amend the paragraph beginning on line 20, as follows:

In order to basically prevent the corrosion of the metal wires formed with an Al or Cu wire according to the present invention, a dummy pattern, where corrosion can occur instead of a main wire pattern, is additionally inserted to a basic wire pattern. When a fine line pattern of sub-micron size is connected to a large pad pattern, the fine line pattern is easily corroded. This corrosion is a dependence of patterns because the large pad pattern and the fine line pattern are formed with the same material. Particularly, when an area ratio of the fine line pattern to the overall wire patterns including the fine line pattern and the large pad pattern is low, [the] corrosion easily occurs. When [so that, as] a dummy fine line pattern is formed, [when] so that an area ratio of the dummy fine line pattern to the entire wire patterns including a fine line pattern, a large pad pattern and the dummy fine line pattern, is larger than an area ratio of the [narrow main] fine line pattern to the entire [wires] wire patterns including the fine line pattern, the large pad pattern, and the dummy fine line pattern, [is formed,] the corrosion of the fine line pattern can be prevented.

IN THE CLAIMS:

Claims 1, 3-5 and 7-11 have been amended as follows:

1. (Amended) A semiconductor device comprising:

a plurality of metal wire patterns[, each of which includes] which include a fine line pattern and pad patterns, [wherein] an area [ratio] of the fine line pattern [to an overall wire pattern is greater] being more than 1% of a total area of said plurality of metal wire patterns.

3. (Amended) The semiconductor device as recited in claim 1, wherein the pad patterns include connection pad patterns which electrically connect the pad patterns to the fine line pattern, said connection pad patterns being included in said [overall wire pattern] total area.

4. (Amended) The semiconductor device as recited in claim 1, wherein the plurality of metal wire patterns are made of aluminum or copper.

5. (Amended) A semiconductor device comprising:

a plurality of metal wire patterns[, each of] which[includes] include main fine line patterns, main pad patterns and dummy fine line patterns, [wherein] an area [ratio] of the dummy fine line patterns, which are connected to the pad patterns, [to an entire wire pattern is] being less than 1% of a total area of said plurality of metal wire patterns and also being less than [and lower than that of] a value obtained by dividing an area [ratio] of the main fine line patterns [to the entire wire pattern] by said total area.

7. (Amended) The semiconductor device as recited in claim 5, wherein the plurality of metal wire patterns are made of aluminum or copper wire.

8. (Amended) The semiconductor device as recited in claim 5, wherein the dummy fine line patterns do not [make] form or contribute to any electric circuit.

9. (Amended) The semiconductor device as recited in claim 5, wherein the plurality of metal wire patterns further include dummy pad patterns, to which the dummy fine line patterns are connected, [wherein the] said dummy pad patterns and [the] said dummy fine line patterns [are] being electrically disconnected from the main fine line patterns and the main pad patterns.

10. (Amended) The semiconductor device as recited in claim 5, wherein the plurality of metal wire patterns further include dummy pad pool patterns, to which the dummy fine line patterns are connected, [wherein the] said dummy pad pool patterns and [the] said dummy fine line patterns [are] being electrically disconnected from the main fine line patterns and the main pad patterns.

11. (Amended) The semiconductor device as recited in claim 5, wherein the plurality of metal wire patterns are made of aluminum or copper wire.